

**Amendment to the Claims:**

1. (Original) A structure of a color filter for use in a liquid crystal display, the color filter structure comprising:

a substrate;

an indium tin oxide layer on the substrate;

a silicon nitride layer on the indium tin oxide layer, wherein a value of an RF power used for growing the silicon nitride layer is a first power value;

an amorphous silicon layer located on the silicon nitride layer;

an n-type silicon layer located on the amorphous silicon layer; and

a metal layer on the n-type silicon layer, wherein a light is emitted into the color filter from the substrate, and after sequentially passing through the substrate, the indium tin oxide layer, the silicon nitride layer, the amorphous silicon layer, and the n-type silicon layer, the light is reflected by the metal layer to be transmitted along an original path for leaving the color filter, wherein the light is absorbed and interfered with by the indium tin oxide layer, the silicon nitride layer, the amorphous silicon layer and the n-type silicon layer, the light being filtered into a specific color light after being emitted from the color filter.

2. (Original) The structure of claim 1, wherein a material of the substrate is glass.

3. (Original) The structure of claim 1, wherein a material of the metal layer comprises chromium.

4. (Currently amended) The structure of claim 3, wherein when the color filter is a black matrix, a thickness of the indium tin oxide layer is about 420 Å, a thickness of the silicon nitride layer is about 500 Å, ~~a thickness of the~~ first power value is about 1.6 KW, a thickness of the amorphous silicon layer is about 500 Å, a thickness of the n-type silicon layer is about 500 Å, and a thickness of the metal layer is about 780 Å.

5. (Currently amended) The structure of claim 3, wherein when the color filter is a reflective blue color filter, a thickness of the indium tin oxide layer is about 420 Å, a thickness of the silicon nitride layer is about 500 Å, ~~a thickness of the~~ first power value is about 2.1 KW, a thickness of the amorphous silicon layer is about 500 Å, a thickness of the n-type silicon layer is about 500 Å, and a thickness of the metal layer is about 780 Å.

6. (Currently amended) The structure of claim 3, wherein when the color filter is a reflective green color filter, a thickness of the indium tin oxide layer is about 168 Å, a thickness of the silicon nitride layer is about 300 Å, ~~a thickness of the~~ first power value is about 1.6 KW, a thickness of the amorphous silicon layer is about 500 Å, a thickness of the n-type silicon layer is about 500 Å, and a thickness of the metal layer is about 780 Å.

7. (Currently amended) The structure of claim 3, wherein when the color filter is a reflective red color filter, a thickness of the indium tin oxide layer is about 420 Å, a thickness of the silicon nitride layer is about 400 Å, ~~a thickness of the~~ first power value

is about 2.1 KW, a thickness of the amorphous silicon layer is about 400 Å, a thickness of the n-type silicon layer is about 400 Å, and a thickness of the metal layer is about 780 Å.

8. (Currently amended) The structure of claim 3, wherein when the color filter is a reflective red color filter, a thickness of the indium tin oxide layer is about 168 Å, a thickness of the silicon nitride layer is about 400 Å, ~~a thickness of the first power value~~ is about 1.6 KW, a thickness of the amorphous silicon layer is about 400 Å, a thickness of the n-type silicon layer is about 400 Å, and a thickness of the metal layer is about 780 Å.

9-24 (Canceled)